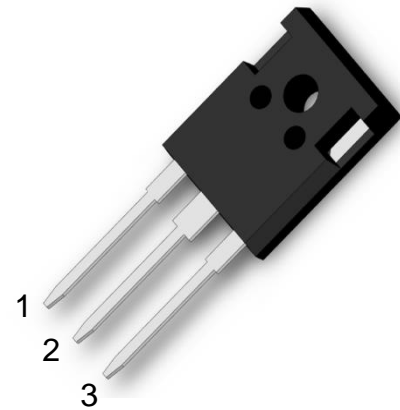


PRODUCT FEATURES

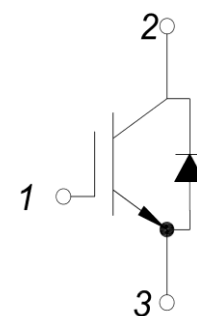
- 650V IGBT chip in trench FS-technology
- Low switching losses
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast switching and short tail current
- Free wheeling diodes with fast and soft reverse recovery



APPLICATIONS

- High frequency switching application
- Medical applications
- Motion/servo control
- UPS systems

1.Gate
2.Collector
3.Emitter



Type	V_{CES}	I_C	$V_{CE(sat)}$ $T_J=25^\circ C$	T_{Jmax}	Marking	Package
MM50G3U65B	650V	50A	1.7V	175°C	MM50G3U65B	TO-247

ABSOLUTE MAXIMUM RATINGS($T_C=25^\circ C$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J=25^\circ C$	V
V_{GES}	Gate Emitter Voltage		
I_C	DC Collector Current	$T_C=25^\circ C$	78
		$T_C=100^\circ C$	50
I_{Cpuls}	Pulsed collector current, tp limited by T_{Jmax}		200
P_{tot}	Power Dissipation Per IGBT		273
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^\circ C$	650
$I_{F(AV)}$	Average Forward Current	$T_C=25^\circ C$	50
I_{Fpuls}	Diode pulsed current, tp limited by T_{Jmax}		200
T_{Jmax}	Max. Junction Temperature		175
T_{Jop}	Operating Temperature		-40~175
T_{stg}	Storage Temperature		-55~150
Torque	to heatsink	Recommended (M3)	1.1
Weight			8

MacMic Science & Technology Co., Ltd.

Add: #18, Hua Shan Zhong Lu, New District, Changzhou City, Jiangsu Province, P. R. of China

Tel.: +86-519-85163708 Fax: +86-519-85162291 Post Code: 213022 Website: www.macmicst.com

MM50G3U65B

IGBT

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=2.0\text{mA}$	4.0	5.0	6.0	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=50\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		1.7	2.05	
		$I_C=50\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		1.9		
		$I_C=50\text{A}, V_{GE}=15\text{V}, T_J=150^\circ\text{C}$		2.05		
I_{CES}	Collector Leakage Current	$V_{CE}=650\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			100	μA
		$V_{CE}=650\text{V}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$			10	mA
I_{GES}	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}, T_J=25^\circ\text{C}$	-200		200	nA
Q_g	Gate Charge	$V_{CE}=400\text{V}, I_C=50\text{A}, V_{GE}=15\text{V}$		250		nC
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		4.9		nF
C_{res}	Reverse Transfer Capacitance				145	pF
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=400\text{V}, I_C=50\text{A}$ $R_G=7.5\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		20	ns
			$T_J=125^\circ\text{C}$		25	ns
			$T_J=150^\circ\text{C}$		25	ns
t_r	Rise Time		$T_J=25^\circ\text{C}$		25	ns
			$T_J=125^\circ\text{C}$		26	ns
			$T_J=150^\circ\text{C}$		26	ns
$t_{d(off)}$	Turn off Delay Time	$T_J=25^\circ\text{C}$		125	ns	
		$T_J=125^\circ\text{C}$		155	ns	
		$T_J=150^\circ\text{C}$		165	ns	
t_f	Fall Time	$T_J=25^\circ\text{C}$		30	ns	
		$T_J=125^\circ\text{C}$		35	ns	
		$T_J=150^\circ\text{C}$		35	ns	
E_{on}	Turn on Energy	$T_J=125^\circ\text{C}$		1	mJ	
		$T_J=150^\circ\text{C}$		1.1	mJ	
E_{off}	Turn off Energy	$T_J=125^\circ\text{C}$		0.95	mJ	
		$T_J=150^\circ\text{C}$		1	mJ	
R_{thJC}	Junction to Case Thermal Resistance (Per IGBT)				0.55	K/W

Anti-Parallel Diode

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=50\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		1.85	2.35	V
		$I_F=50\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.65		
		$I_F=50\text{A}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$		1.55		
t_{rr}	Reverse Recovery Time	$I_F=50\text{A}, V_R=400\text{V}$ $di_F/dt=-2000\text{A}/\mu\text{s}$ $T_J=150^\circ\text{C}$		120		ns
I_{RRM}	Max. Reverse Recovery Current			50		A
Q_{RR}	Reverse Recovery Charge			3.3		μC
E_{rec}	Reverse Recovery Energy			1		mJ
R_{thJCD}	Junction to Case Thermal Resistance (Per Diode)				1.1	K/W

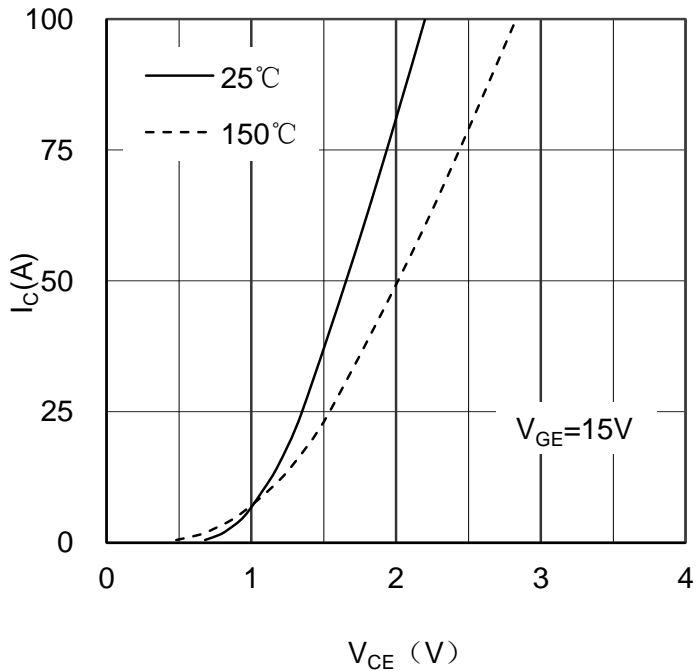


Figure 1. Typical Output Characteristics IGBT

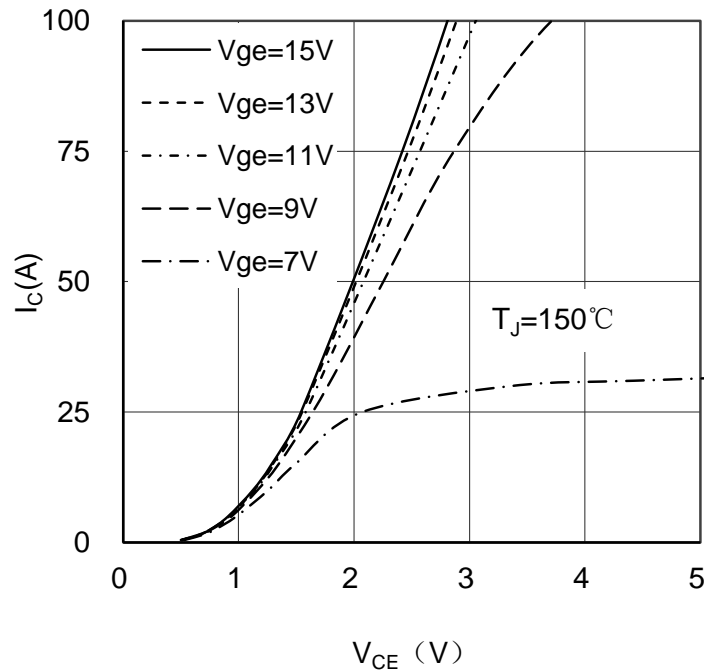


Figure 2. Typical Output Characteristics IGBT

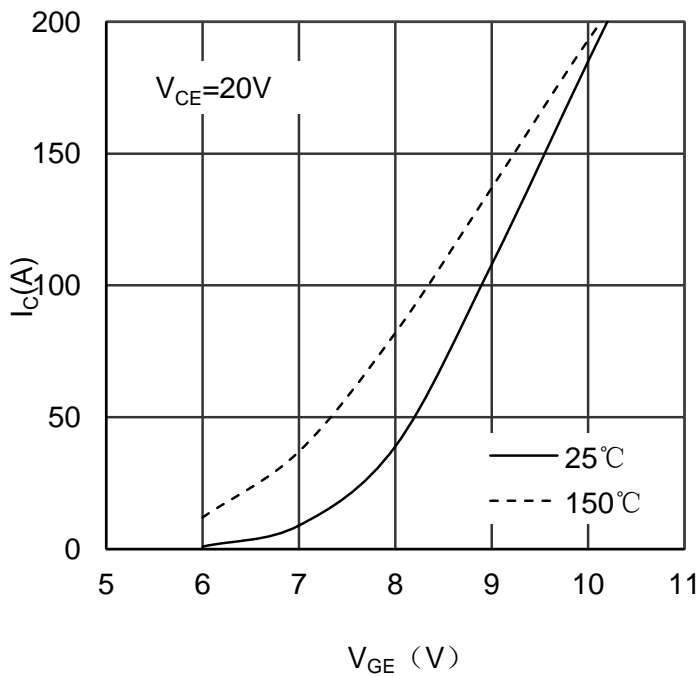


Figure 3. Typical Transfer characteristics IGBT

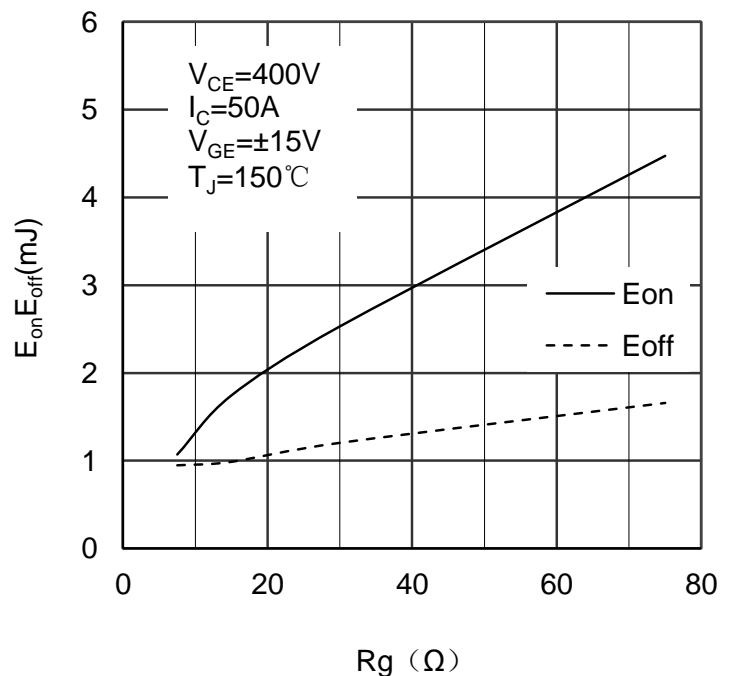


Figure 4. Switching Energy vs Gate Resistor IGBT

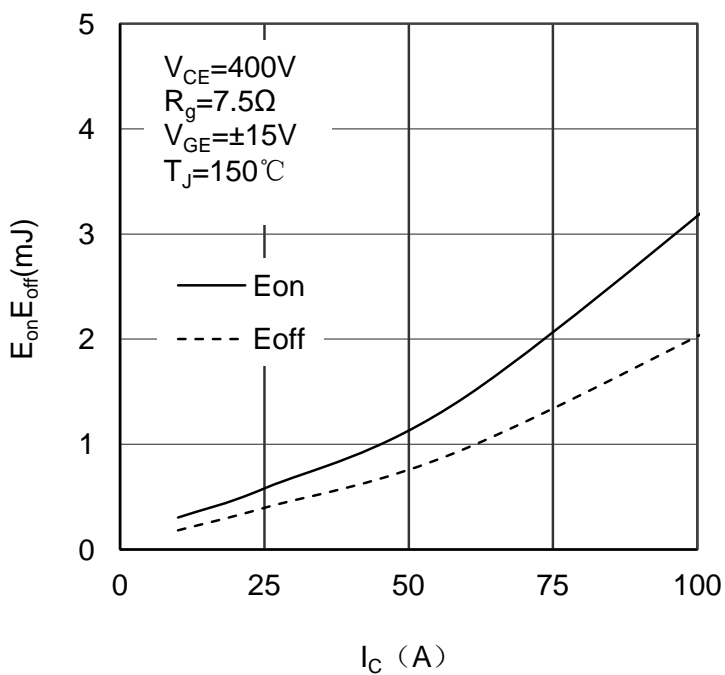


Figure 5. Switching Energy vs Collector Current IGBT

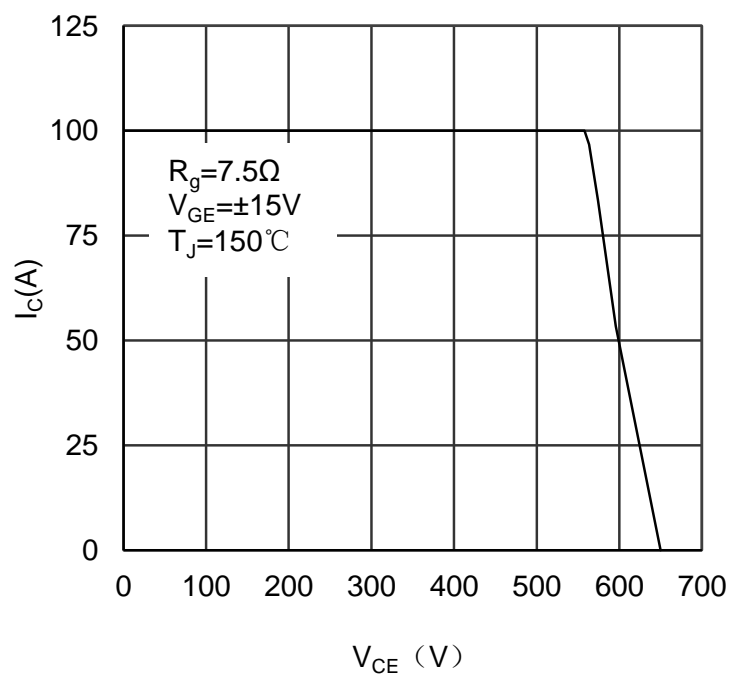


Figure 6. Reverse Biased Safe Operating Area IGBT

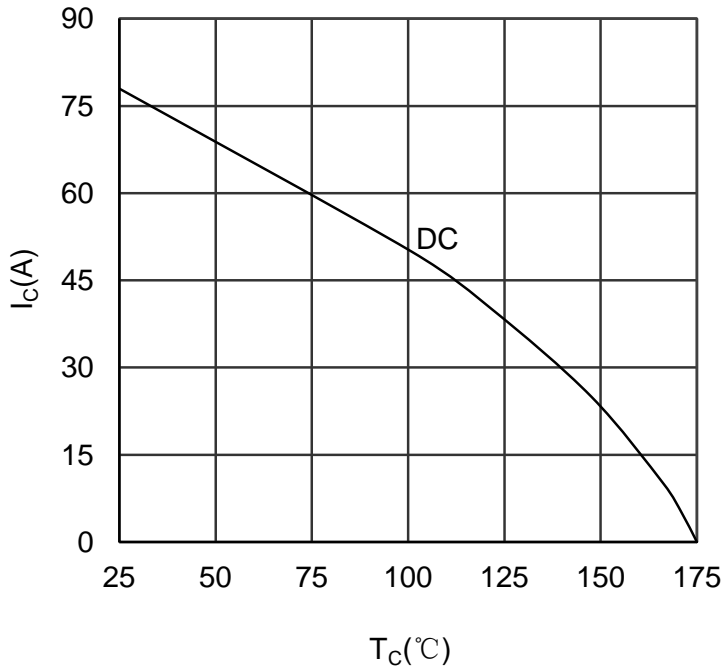


Figure 7. Collector Current vs Case temperature IGBT

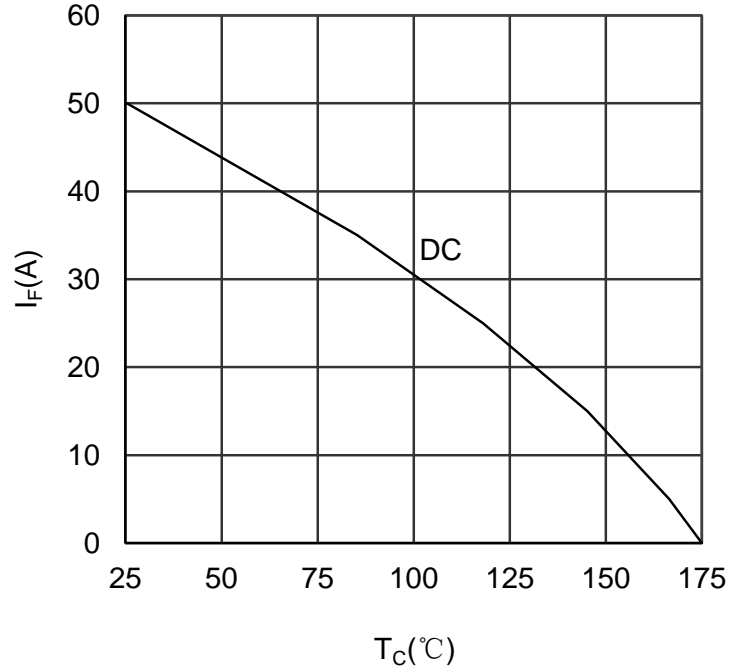


Figure 8. Forward current vs Case temperature Diode

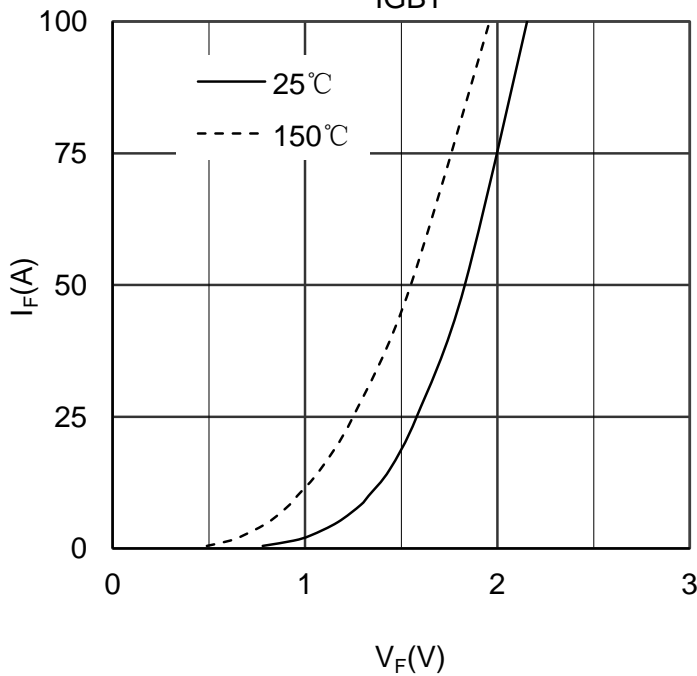


Figure 9. Diode Forward Characteristics Diode

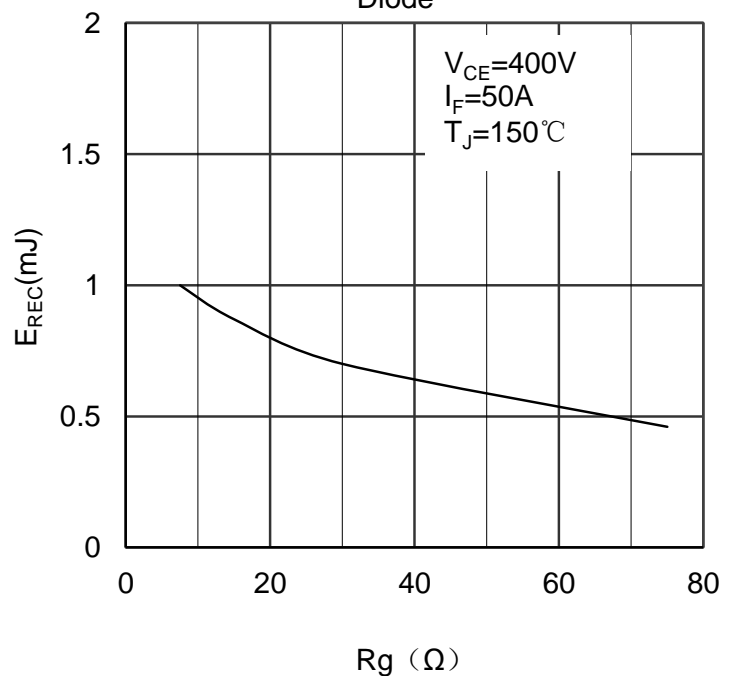


Figure 10. Switching Energy vs Gate Resistor Diode

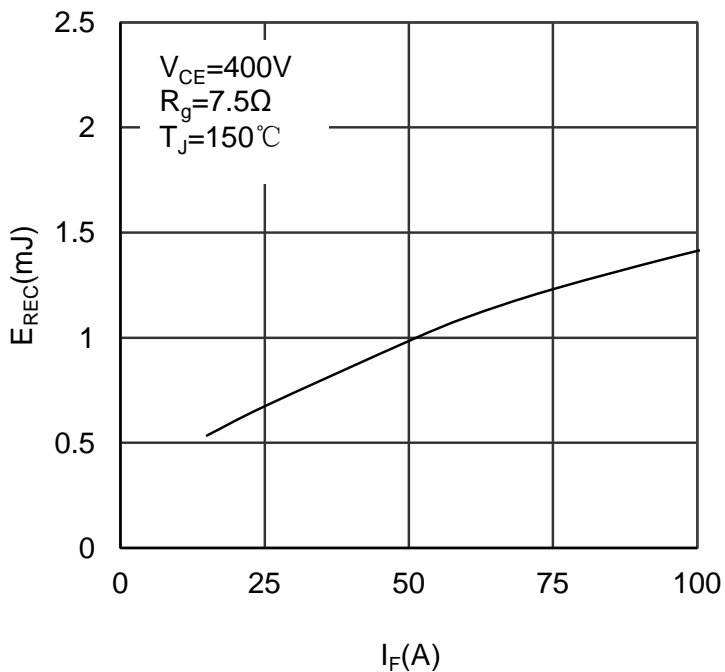


Figure 11. Switching Energy vs Forward Current Diode

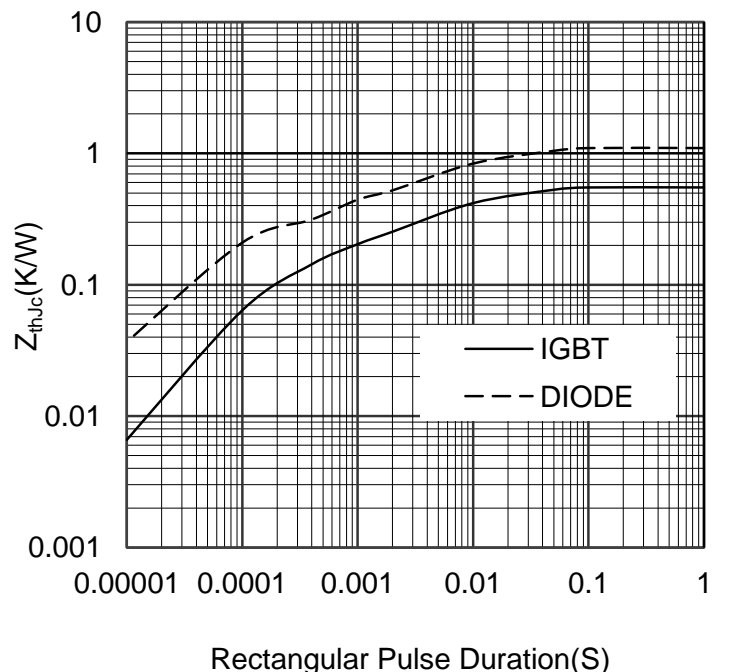
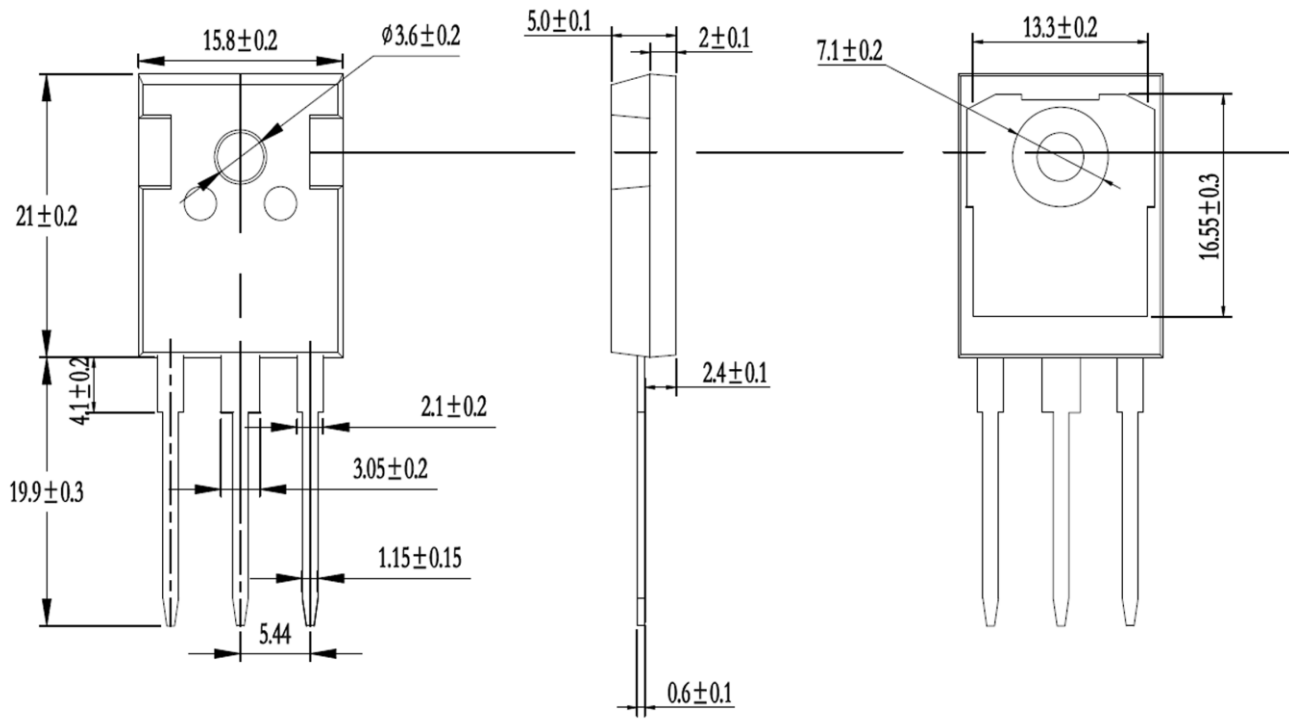


Figure 12. Transient Thermal Impedance of Diode and IGBT



Dimensions in (mm)
Figure 13. Package Outline